

Features

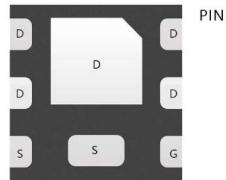
- Excellent package for good heat dissipation
- Ultra low gate charge
- Low reverse transfer capacitance
- Fast switching capability
- Avalanche energy specified

Application

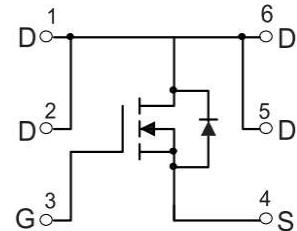
- Power switching application

Product Summary

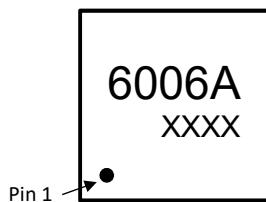
V _{DS}	R _{DS(ON)} MAX	I _D MAX
60V	44mΩ@10V	6A
	53mΩ@4.5V	



DFN2X2-6L view



Schematic diagram



6006A : Device code
XXXX: Code
Solid dot: Pin1 indicator

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V _{DS}	Drain-Source Breakdown Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
T _J	Maximum Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C 6	A
Mounted on Large Heat Sink			
I _{DM}	Pulse Drain Current Tested	Tc=25°C 24	A
I _D	Continuous Drain Current	Tc=25°C 6	A
P _D	Maximum Power Dissipation	Tc=25°C 1.96	W
R _{θJA}	Thermal Resistance Junction-Ambient	83.5	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLSM6006A	DFN2X2-6L	6006A	3,000	45,000	180,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.5	--	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =6A	--	36	44	mΩ
		V _{GS} =4.5V, I _D =4A	--	42	53	mΩ

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

C _{ISS}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	--	1020	--	pF
C _{OSS}	Output Capacitance		--	70	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	60	--	pF

Switching Characteristics

Q _g	Total Gate Charge	V _{DS} =30V, I _D =6A, V _{GS} =10V	--	26.5	--	nC
Q _{gs}	Gate Source Charge		--	5.5	--	nC
Q _{gd}	Gate Drain Charge		--	6.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =6A, V _{GS} =10V, R _G =2.3Ω	--	10	--	nS
t _r	Turn-on Rise Time		--	20	--	nS
t _{d(off)}	Turn-Off Delay Time		--	30	--	nS
t _f	Turn-Off Fall Time		--	21	--	nS

Source- Drain Diode Characteristics

V _{SD}	Forward on voltage	T _j =25°C, I _S =6A	--	--	1.2	V
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Typical Operating Characteristics

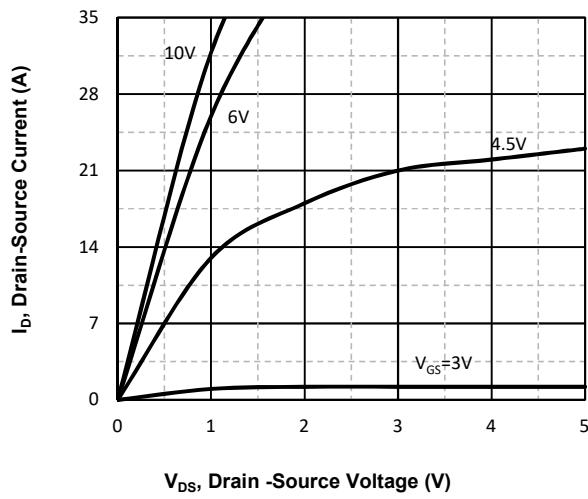


Fig1. Typical Output Characteristics

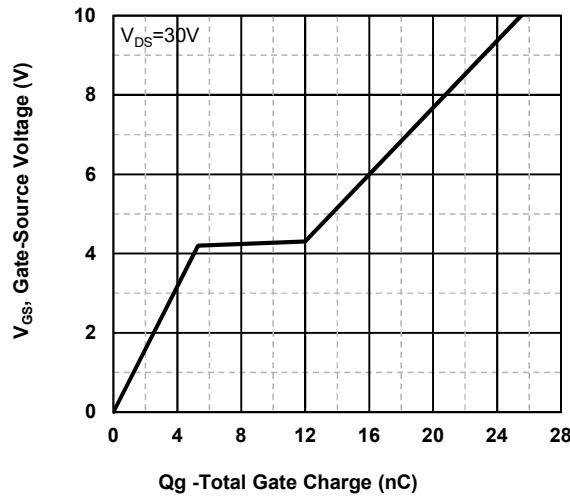


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

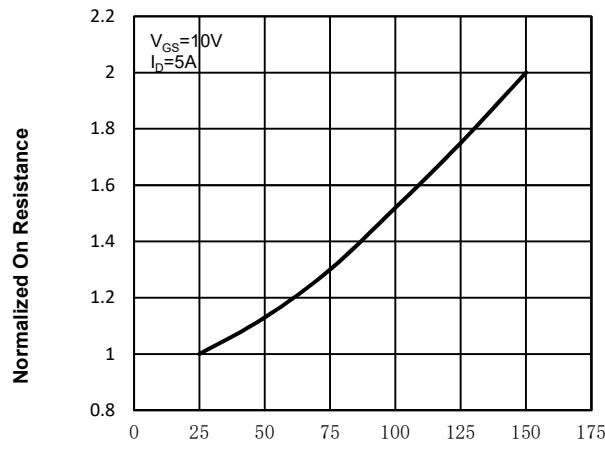


Fig3. Normalized On-Resistance Vs. Temperature

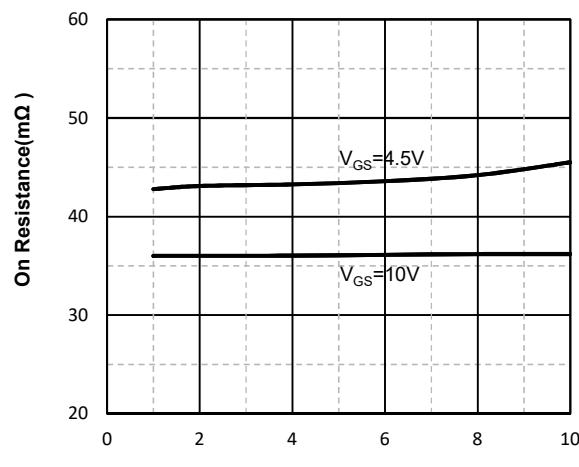


Fig4. On-Resistance Vs. Drain-Source Current

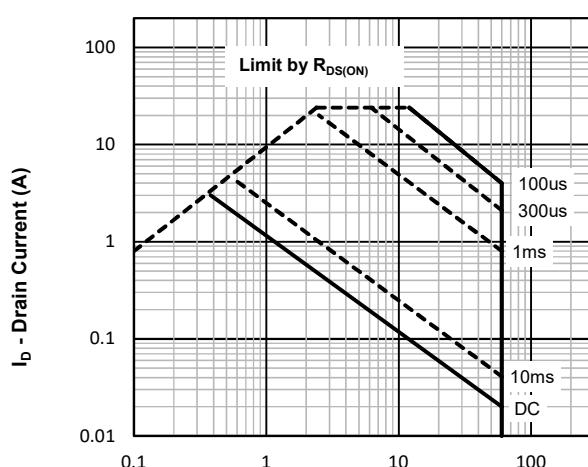


Fig5. Maximum Safe Operating Area

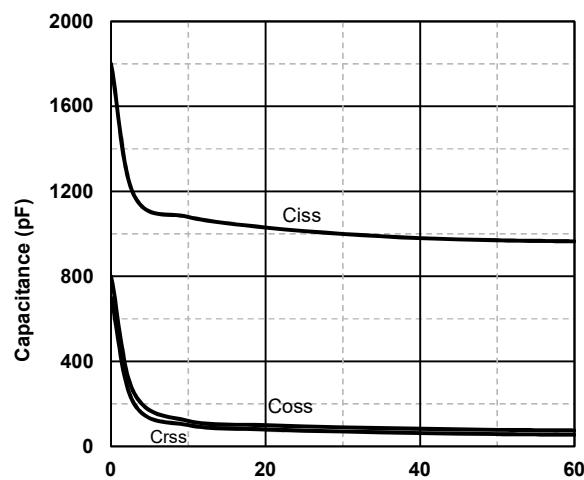
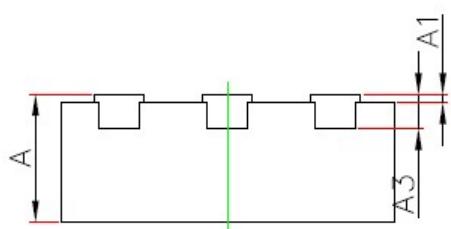
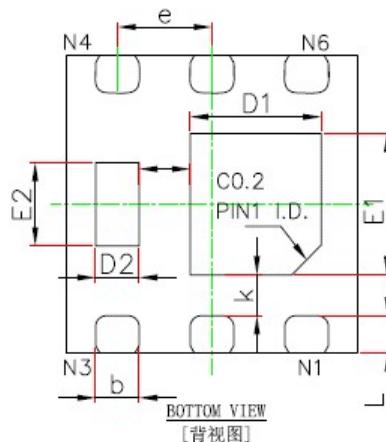
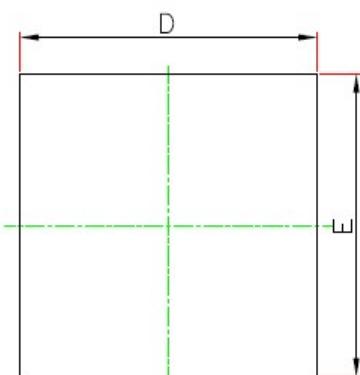


Fig6 Typical Capacitance Vs.Drain-Source Voltage

DFN2X2-6L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.600	0.700	0.023	0.027
A1	0.000	0.050	0.000	0.001
A3	0.203REF		0.007REF	
b	0.315	0.415	0.012	0.016
D	1.924	2.076	0.075	0.081
E	1.924	2.076	0.075	0.081
e	0.650TYP		0.225TYP	
L	0.224	0.376	0.008	0.014
k	0.200	-	0.007	-
E1	1.000	1.200	0.039	0.047
D1	0.900	1.100	0.035	0.043
E2	0.700	0.900	0.027	0.035
D2	0.150	0.350	0.005	0.013